ISA08N80A

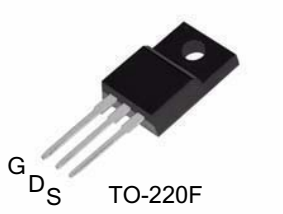
N-Channel MOSFET

Lead Free Package and Finish

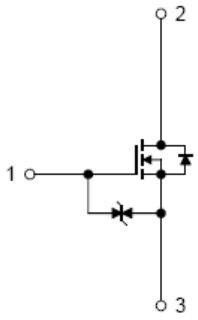
Applications:
- ATX Power
- LCD Panel Power

V_{DSS}	$R_{DS(on)}$(Typ)	I_D (Max)
800V	1.0Ω	8.0A

Features:
- RoHS Compliant & Halogen Free
- Low ON Resistance
- Low Gate Charge
- ESD Capability Improved



Packages
Not to Scale



1. GATE
2. DRAIN (HEATSINK)
3. SOURCE

Ordering Information

Part Number	Package Type	Brand
ISA08N80A	TO-220F	IPS

Absolute Maximum Ratings Tc= 25℃ unless otherwise specified

Symbol	Parameter	Maximum	Units
V_{DSS}	Drain-to-Source Voltage (NOTE *1)	800	V
I_D	Continuous Drain Current	8.0	A
I_D@ 100 ℃	Continuous Drain Current	Figure3	
I_{DM}	Pulsed Drain Current, V_{GS}@ 10V (NOTE *2)	Figure6	
P_D	Power Dissipation	45	W
	Derating Factor above 25℃	0. 36	W/C
V_{GS}	Gate-to-Source Voltage	±30	V
EAS	Single Pulse Avalanche Engergy;	320	mJ
$V_{ESD(GS)}$	Gate Source ESD Voltage(HBM,c=100pF,R=1.5K Ω)	6000	V
dv/dt	Peak Diode Recovery dv/dt (NOTE *3)	5.0	V/ns
T_L T_{PKG}	Maximum Temperature for Soldering Leads at 0.063in(1.6mm) from Case for 10 seconds Package Body for 10 seconds	300 260	℃
T_J and T_{STG}	Operation Junction and Storage Temperature Range	150, -55 to 150	℃

Caution: *Stresses greater than those listed in "Absolute Maximum Ratings" Table may cause permanent damage to the device.*

Thermal Resistance

Symbol	Parameter	Maximum	Units	Test Condition
$R_{\theta JC}$	Junction-to-Case	2.78	℃/W	Drain lead soldered to water cooled heatsink, PD ad-justed for a peak junction temperature of +150oC. 1 cubic foot chamber, free air.
$R_{\theta JA}$	Junction-to-Ambient	100		

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Electrical Characteristics TJ= 25℃ unless otherwise specified：

OFF Characteristics						
Symbol	Parameter	Rating			Units	Test Conditions
		Min.	Typ.	Max.		
V_{DSS}	Drain-to-Source Breakdown Voltage	800	--	--	V	V_{GS}=0V, I_D=250μA
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	--	0.5	--	V/℃	Reference to 25℃, ID=250uA
$I_{DS(off)}$	Off-State Drain-to-Source Current	--	--	1.0	uA	V_{DS} = 800V, V_{GS}=0V, T_a = 25℃
		--	--	100		V_{DS} =640V, V_{GS}= 0 V, T_a = 125℃
$I_{GSS(F)}$	Gate-to-Source Forward Leakage	--	--	1.0	uA	V_{GS} =+20V
$I_{GSS(R)}$	Gate-to-Source Reverse Leakage	--	--	-1.0		V_{GS} =-20V

ON Characteristics						
Symbol	Parameter	Rating			Units	Test Conditions
		Min.	Typ.	Max.		
$R_{DS(ON)}$	Drain-to-Source On-Resistance	--	1.0	1.25	Ω	V_{GS}=10V,I_D=4.8A (NOTE*4)
g_{fs}	Forward Transconductance	--	16	--	S	|V_{DS}|>2I_D*$R_{DS(on)max}$ I_D =10A (NOTE*4)
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS} = V_{GS}, I_D = 250μA

Dynamic Characteristics						
Symbol	Parameter	Rating			Units	Test Conditions
		Min.	Typ.	Max.		
C_{iss}	Input Capacitance	--	2050	--	pF	V_{GS} =0V V_{DS} = 25V f = 1.0MHz
C_{oss}	Output Capacitance	--	150	--		
C_{rss}	Reverse Transfer Capacitance	--	20	--		
Q_g	Total Gate Charge	--	48	--	nC	V_{DD} =400V I_D =8.0A Vgs=10V
Q_{gs}	Gate-to-Source Charge	--	8	--		
Q_{gd}	Gate-to-Drain (“Miller”)Charge	--	18	--		

Resistive Switching Characteristics						
Symbol	Parameter	Rating			Units	Test Conditions
		Min.	Typ.	Max.		
$t_{d(ON)}$	Turn-on Delay Time	--	25	--	ns	V_{DD} = 400V I_D =8.0A V_{GS} = 10V R_G =25Ω
trise	Rise Time	--	43	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	135	--		
t_{fall}	Fall Time	--	62	--		

Source-Drain Diode Characteristics						
Symbol	Parameter	Rating			Units	Test Conditions
		Min.	Typ.	Max.		
I_S	Continuous Source Current (Body Diode)	--	--	8.0	A	Integral pn-diode in MOSFET
I_{SM}	Maximum Pulsed Current (Body Diode)	--	--	32	A	
V_{SD}	Diode Forward Voltage	--	--	1.5	V	I_S=8A,V_{GS}=0V
trr	Reverse Recovery Time	--	550	--	nS	I_F=8A, T_j = 25°C di/dt=100A/us
Qrr	Reverse Recovery Charge	--	3.6	--	uC	

Notes:

***1.** T_J=+25℃ to +150℃.

***2.** Repetitive rating; pulse width limited by maximum junction temperature.

***3.** I_{SD}=8.0A di/dt≤100A/us, V_{DD}≤BV_{DSS}, T_{Jmax}=+150℃.

***4.** Pulse width≤380us; duty cycle≤2%.

Characteristics Curve:

Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case

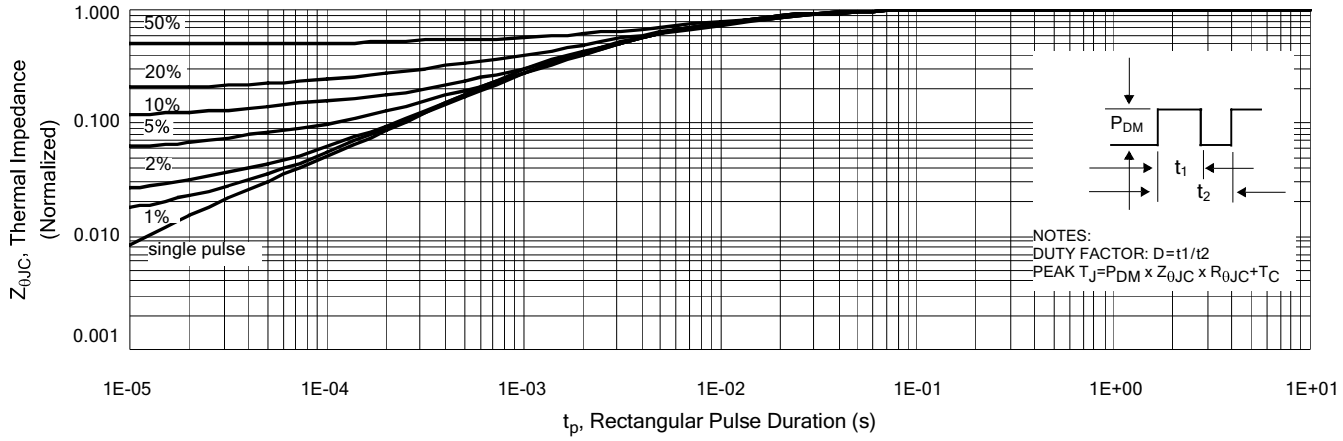


Figure 2. Maximum Power Dissipation vs Case Temperature

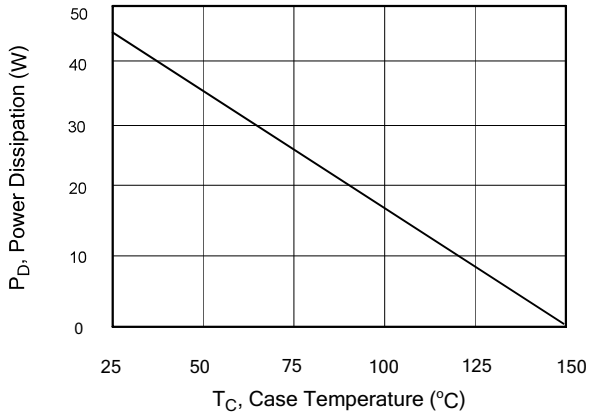


Figure3. Maximum Continuous Drain Current vs Case Temperature

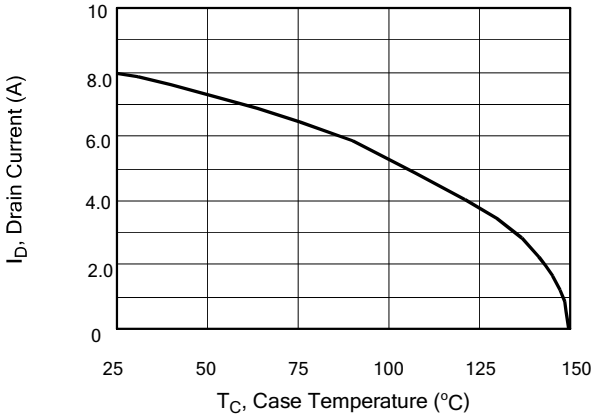


Figure 4. Typical Output Characteristics

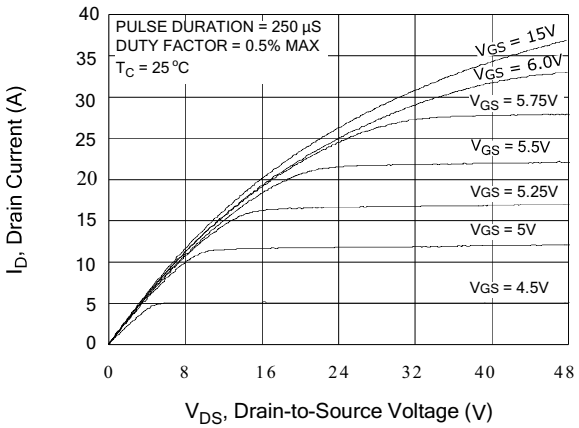


Figure5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current

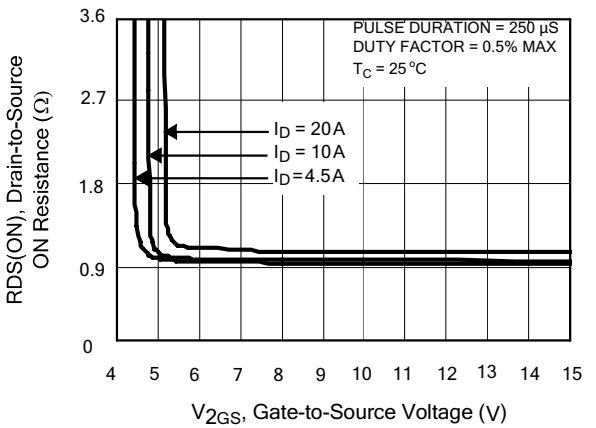


Figure 6. Maximum Peak Current Capability

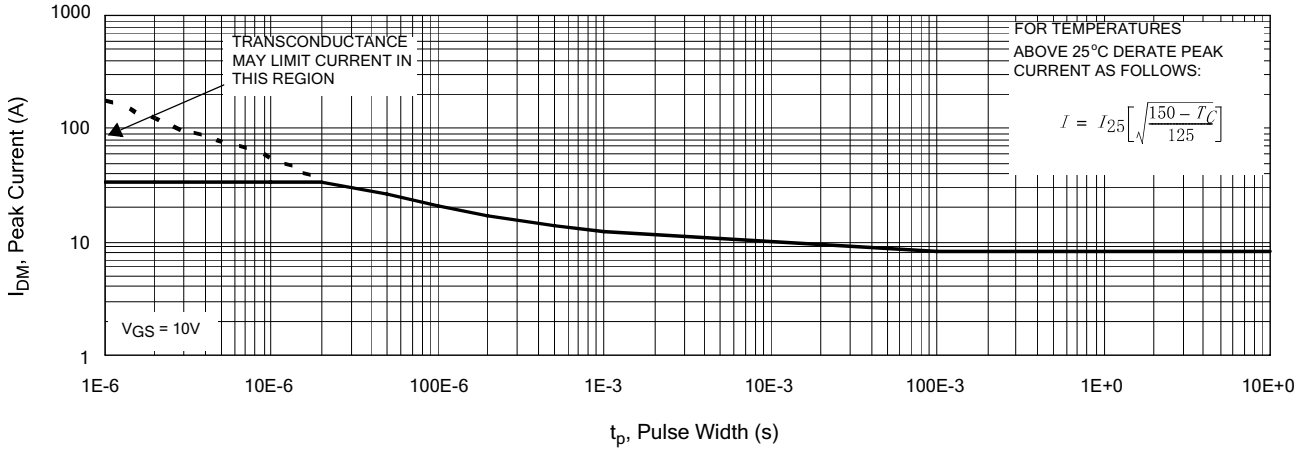


Figure 7. Typical Transfer Characteristics

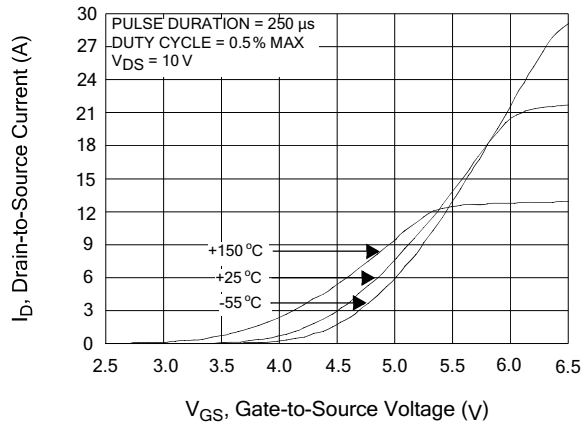


Figure8. Unclamped Inductive Switching Capability

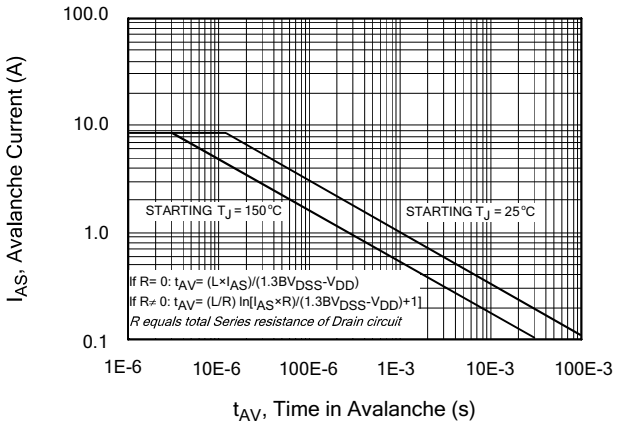


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

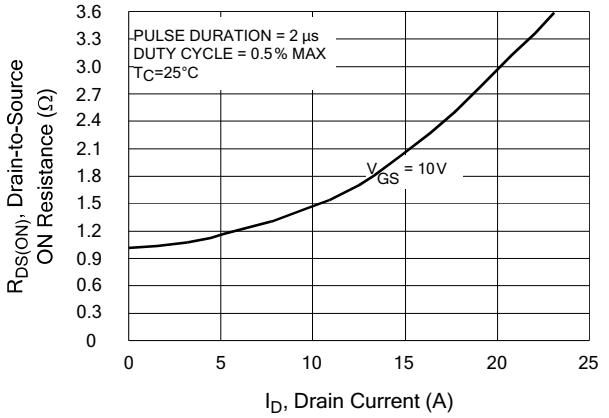


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature

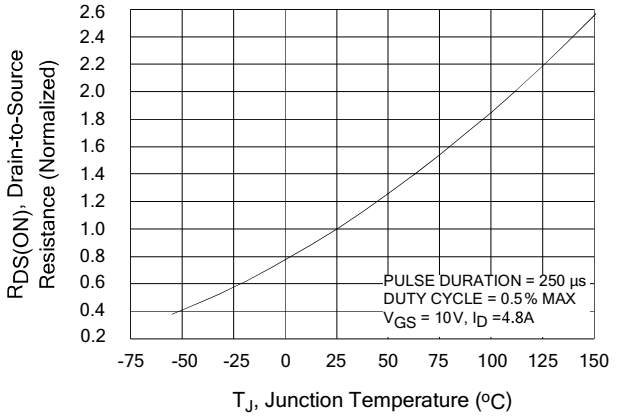


Figure 11. Typical Breakdown Voltage vs Junction Temperature

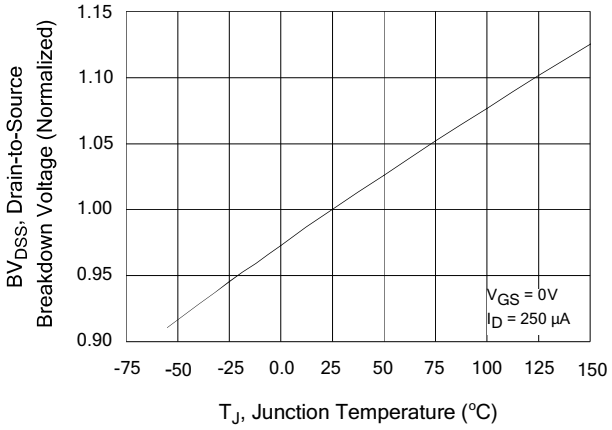


Figure 12. Typical Threshold Voltage vs Junction Temperature

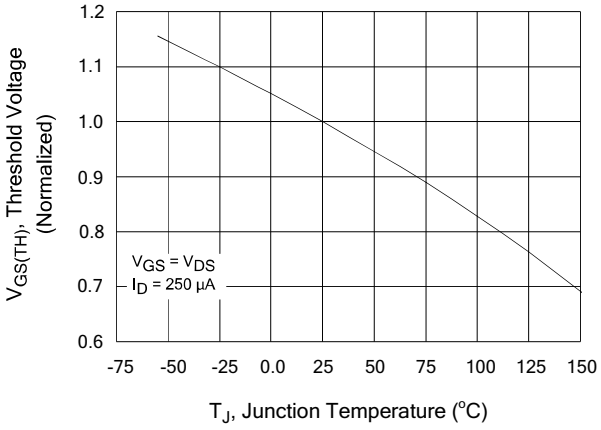


Figure 13. Maximum Forward Bias Safe Operating Area

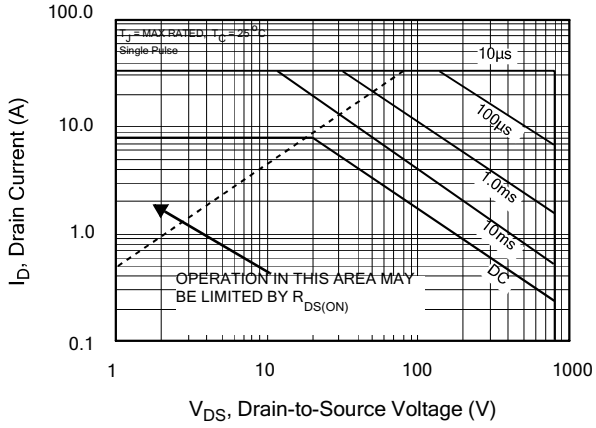


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

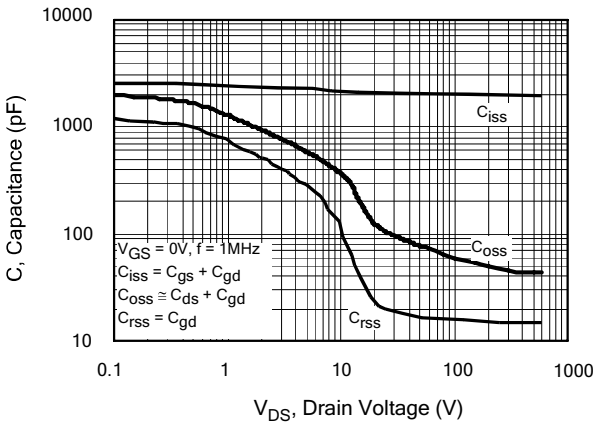


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

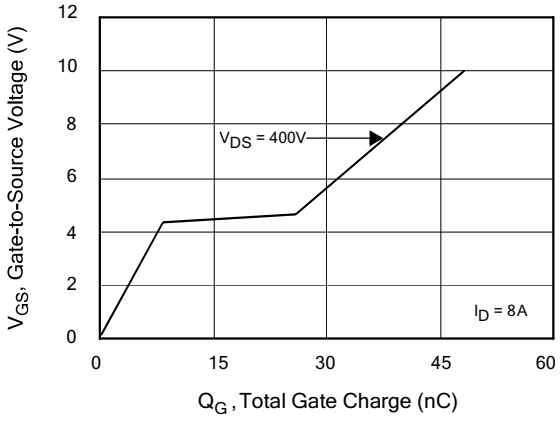
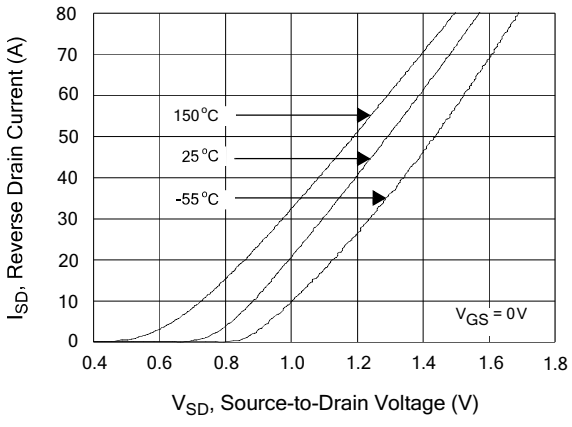


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuits and Waveforms

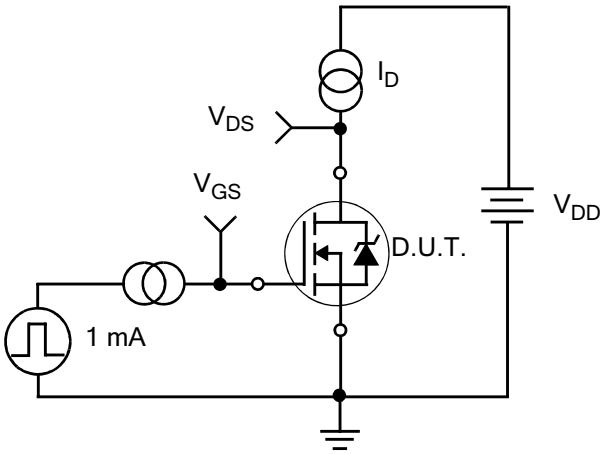


Figure 17. Gate Charge Test Circuit

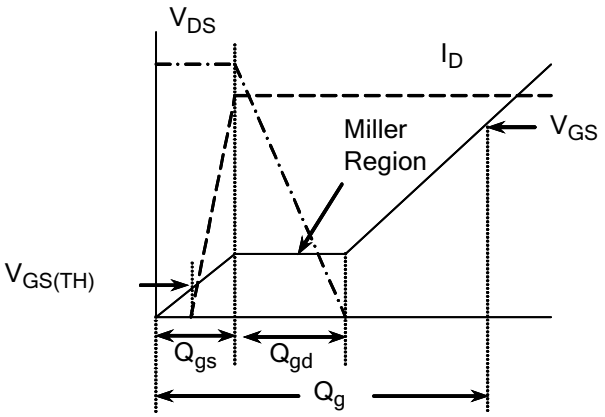


Figure 18. Gate Charge Waveform

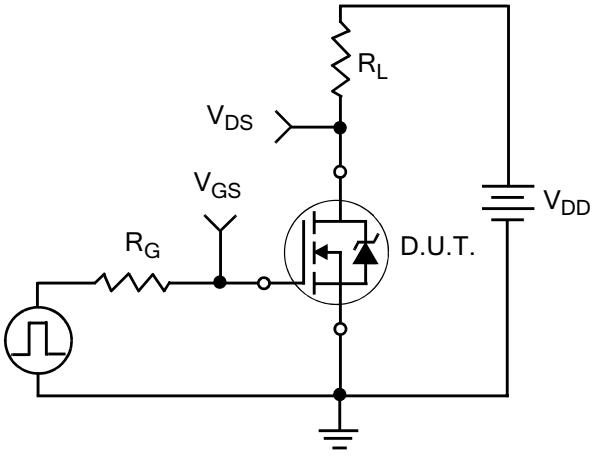


Figure 19. Resistive Switching Test Circuit

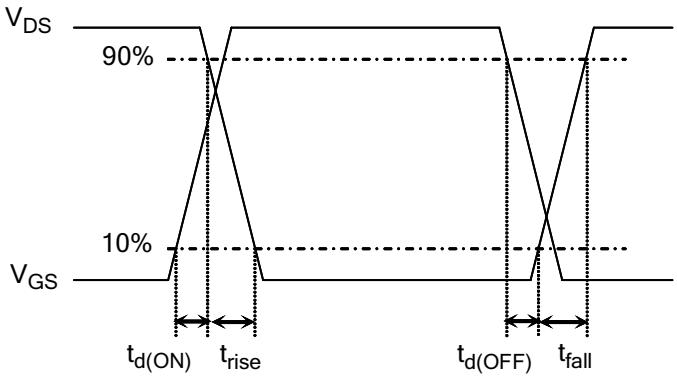


Figure 20. Resistive Switching Waveforms

Test Circuits and Waveforms

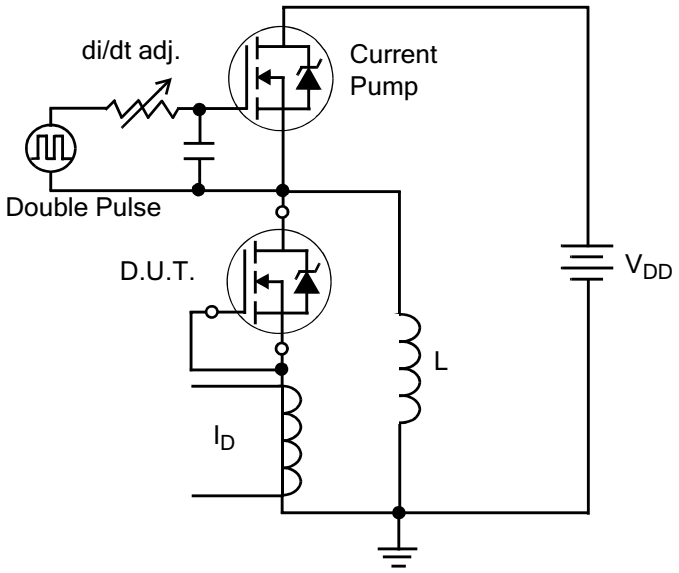


Figure 21. Diode Reverse Recovery Test Circuit

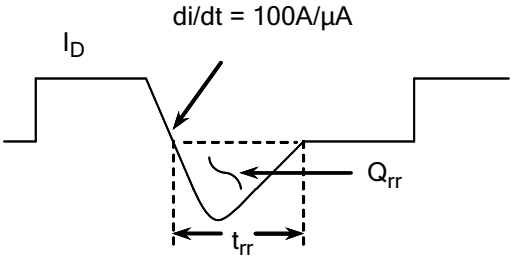


Figure 22. Diode Reverse Recovery Waveform

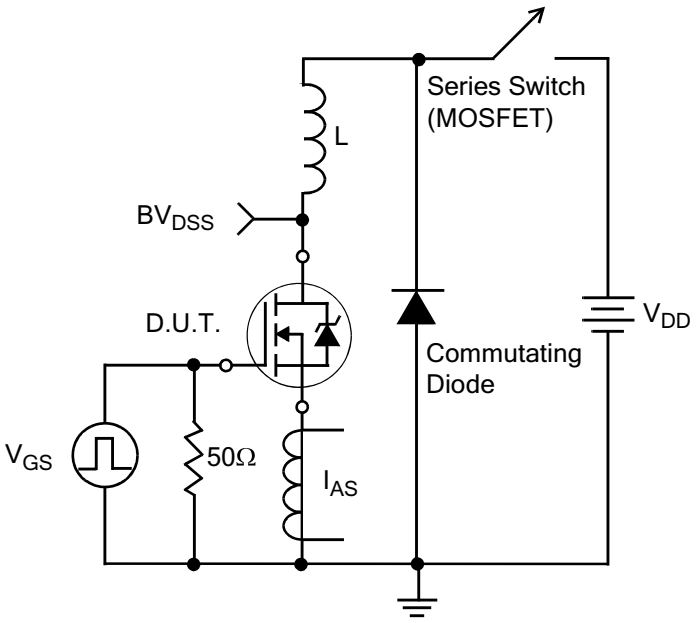
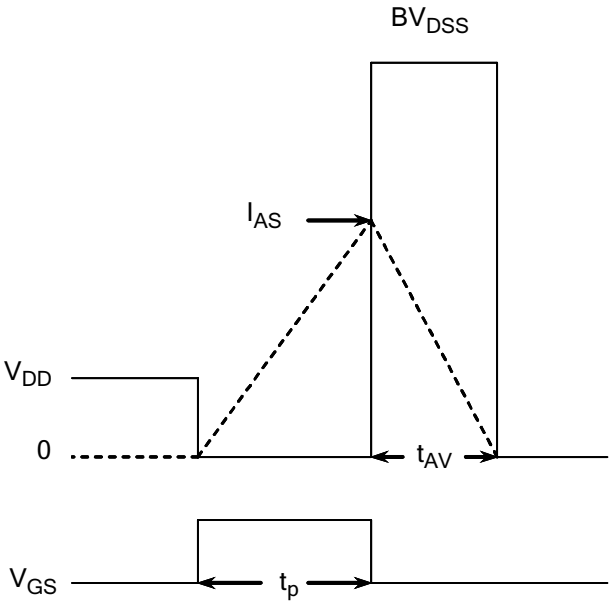


Figure 23. Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

Figure 24. Unclamped Inductive Switching Waveforms

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